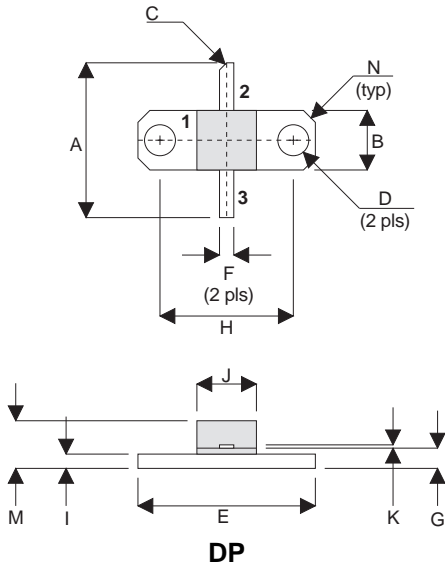


**MECHANICAL DATA**

**GOLD METALLISED  
MULTI-PURPOSE SILICON  
DMOS RF FET  
2.5W – 12.5V – 1GHz  
SINGLE ENDED**



PIN 1 SOURCE                      PIN 2 DRAIN  
PIN 3 GATE

**FEATURES**

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

**APPLICATIONS**

- VHF/UHF COMMUNICATIONS  
from 1 MHz to 1 GHz

DIM	mm	Tol.	Inches	Tol.
A	16.51	0.25	0.650	0.010
B	6.35	0.13	0.250	0.005
C	45°	5°	45°	5°
D	3.30	0.13	0.130	0.005
E	18.92	0.08	0.745	0.003
F	1.52	0.13	0.060	0.005
G	2.16	0.13	0.085	0.005
H	14.22	0.08	0.560	0.003
I	1.52	0.13	0.060	0.005
J	6.35	0.13	0.250	0.005
K	0.13	0.03	0.005	0.001
M	5.08	0.51	0.200	0.020
N	1.27 x 45°	0.13	0.050 x 45°	0.005

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}\text{C}$  unless otherwise stated)

$P_D$	Power Dissipation	17.5W
$BV_{DSS}$	Drain – Source Breakdown Voltage	40V
$BV_{GSS}$	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	2A
$T_{stg}$	Storage Temperature	$-65$ to $150^{\circ}\text{C}$
$T_j$	Maximum Operating Junction Temperature	$200^{\circ}\text{C}$

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## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
B <sub>V</sub> DSS Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0      I <sub>D</sub> = 10mA	40			V
I <sub>D</sub> DSS Zero Gate Voltage Drain Current	V <sub>DS</sub> = 12.5V      V <sub>GS</sub> = 0			1	mA
I <sub>G</sub> SS Gate Leakage Current	V <sub>GS</sub> = 20V      V <sub>DS</sub> = 0			1	μA
V <sub>GS(th)</sub> Gate Threshold Voltage*	I <sub>D</sub> = 10mA      V <sub>DS</sub> = V <sub>GS</sub>	1		7	V
g <sub>fs</sub> Forward Transconductance*	V <sub>DS</sub> = 10V      I <sub>D</sub> = 0.2A	0.18			S
G <sub>PS</sub> Common Source Power Gain	P <sub>O</sub> = 2.5W	10			dB
η Drain Efficiency	V <sub>DS</sub> = 12.5V      I <sub>DQ</sub> = 0.1A	40			%
VSWR Load Mismatch Tolerance	f = 1GHz	20:1			—
C <sub>iss</sub> Input Capacitance	V <sub>DS</sub> = 0      V <sub>GS</sub> = -5V      f = 1MHz			12	pF
C <sub>oss</sub> Output Capacitance	V <sub>DS</sub> = 12.5V      V <sub>GS</sub> = 0      f = 1MHz			10	pF
C <sub>rss</sub> Reverse Transfer Capacitance	V <sub>DS</sub> = 12.5V      V <sub>GS</sub> = 0      f = 1MHz			1	pF

\* Pulse Test:    Pulse Duration = 300 μs , Duty Cycle ≤ 2%

## HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

## THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 10°C / W
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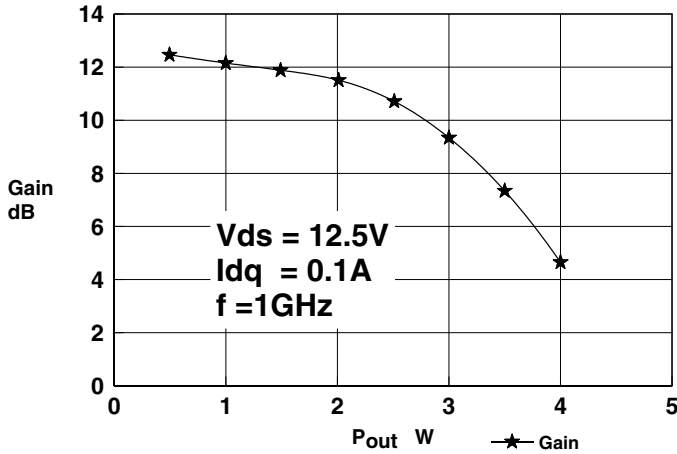


Figure 1- Gain vs. Power Output

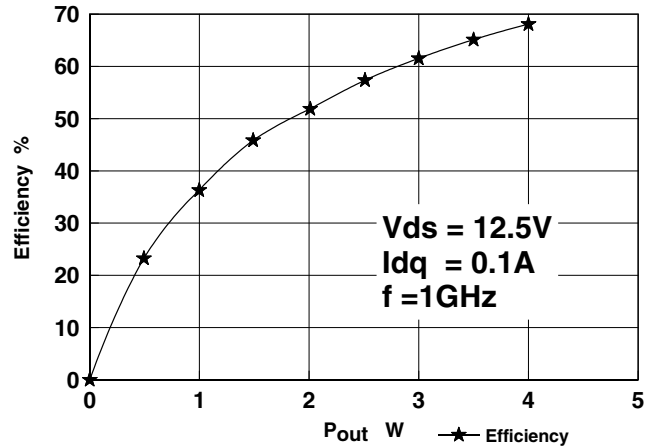


Figure 2 - Efficiency vs Power Output

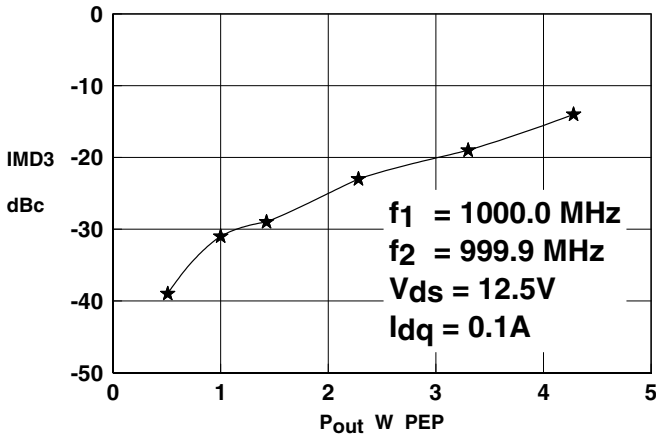


Figure 3 - IMD vs Power Output

OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z <sub>S</sub> Ω	Z <sub>L</sub> Ω
1000MHz	2.8 + j3.0	8.0 - j2.0

Typical S Parameters

! V<sub>DS</sub> = 12.5V, I<sub>DQ</sub> = 0.2A  
 # MHz S M A R 50

Freq MHz	S11		S21		S12		S22	
	mag	ang	mag	ang	mag	ang	mag	ang
50	0.95	-38.2	16.3	160.6	0.015	67.2	0.90	-34.4
100	0.89	-55.9	14.0	139.3	0.026	49.3	0.86	-55.4
150	0.84	-75.2	11.8	122.1	0.032	33.6	0.80	-74.8
200	0.80	-90.6	9.5	107.5	0.034	23.1	0.77	-89.6
250	0.78	-99.5	8.2	97.1	0.035	13.1	0.76	-97.9
300	0.76	-109.8	6.9	92.1	0.035	11.0	0.75	-106.7
350	0.76	-115.0	6.2	80.9	0.035	2.4	0.76	-113.0
400	0.76	-121.6	5.2	74.0	0.031	-2.8	0.76	-119.5
450	0.76	-126.4	4.7	74.9	0.030	0.1	0.77	-123.3
500	0.76	-131.1	4.1	67.7	0.028	-4.6	0.78	-127.5
550	0.77	-135.4	3.8	65.3	0.026	-3.1	0.79	-131.5
600	0.77	-139.6	3.6	60.1	0.024	-4.1	0.79	-135.0
650	0.77	-142.8	3.2	53.9	0.021	-4.9	0.80	-137.9
700	0.74	-148.1	2.6	52.5	0.017	0.4	0.75	-140.6
750	0.76	-148.4	3.0	52.2	0.018	8.5	0.81	-141.2
800	0.77	-153.1	2.8	46.2	0.017	14.5	0.81	-144.1
850	0.77	-155.8	2.6	40.0	0.016	22.0	0.82	-146.2
900	0.77	-159.4	2.4	35.4	0.016	31.0	0.82	-148.5
950	0.77	-163.8	2.3	32.3	0.017	40.7	0.83	-150.7
1000	0.76	-167.7	2.2	29.7	0.017	51.3	0.82	-153.1
1050	0.76	-170.9	2.2	24.6	0.020	58.8	0.83	-155.6

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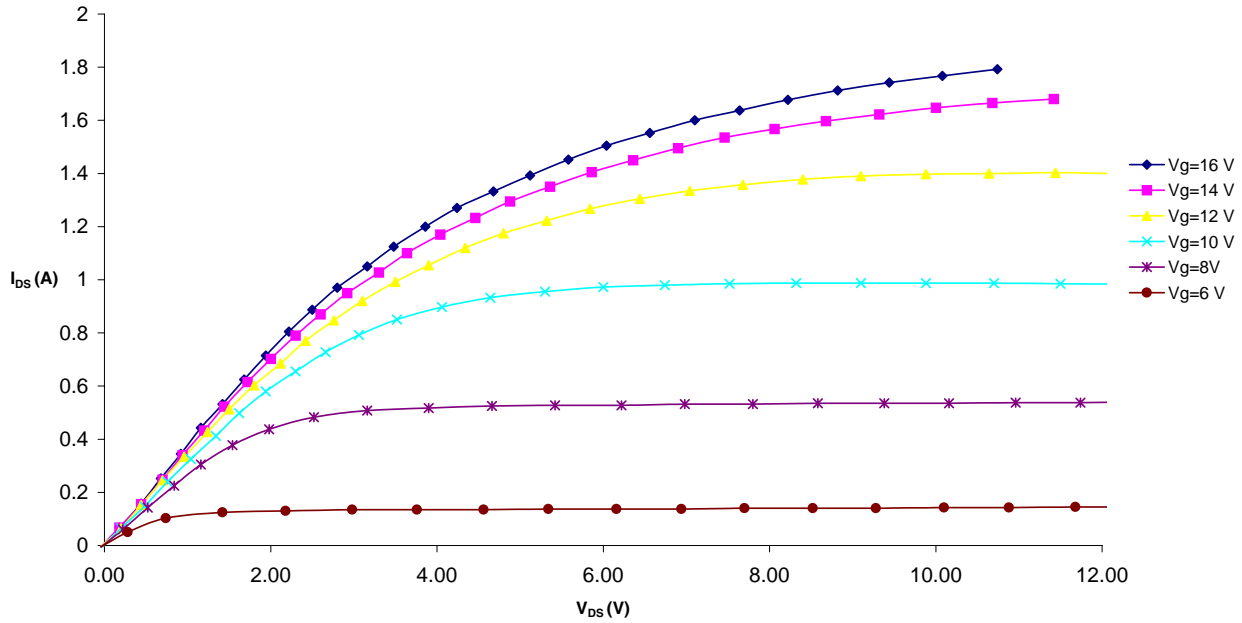


Figure 4 – Typical IV Characteristics.

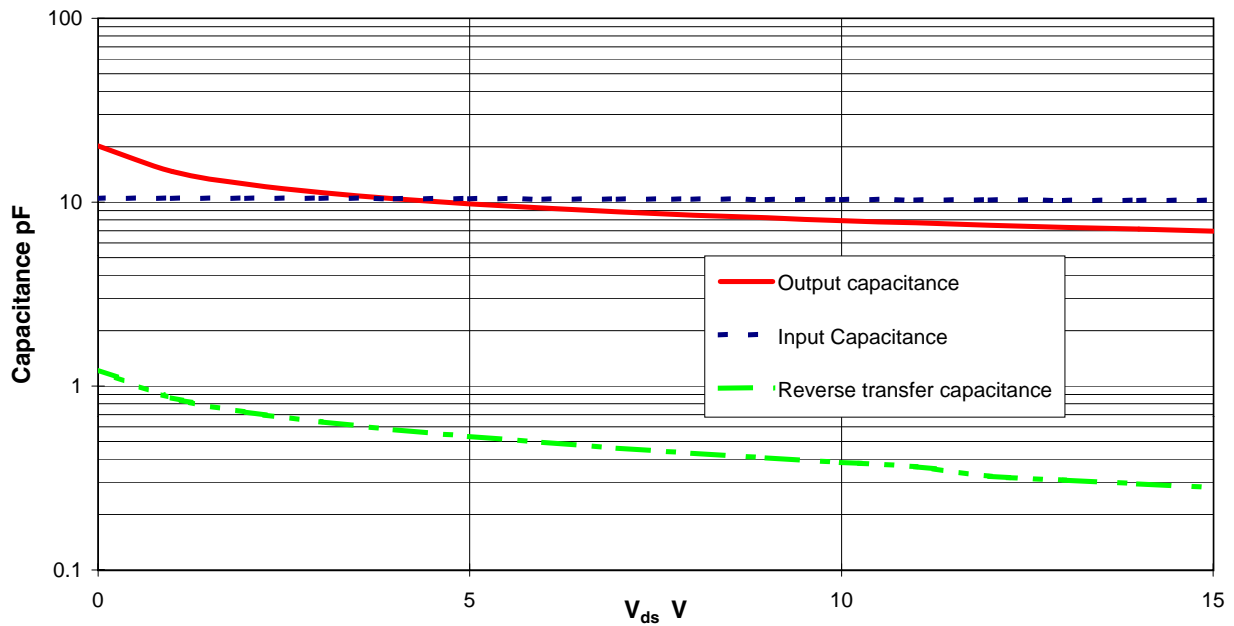
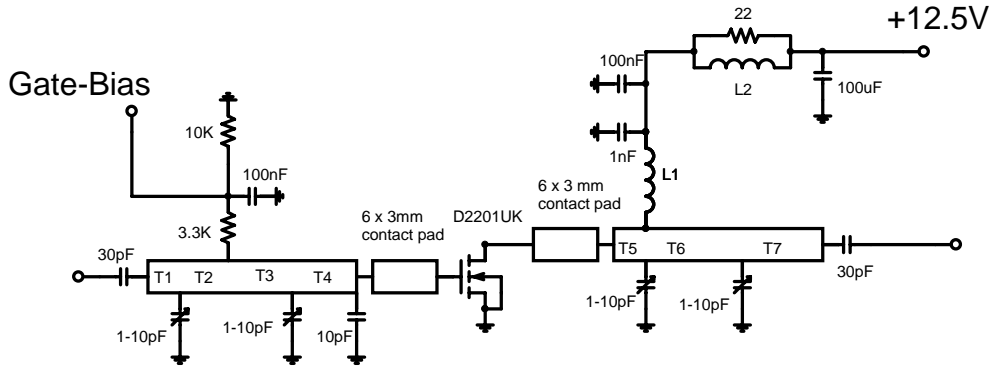


Figure 5 – Typical CV Characteristics.

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Substrate 0.8mm PTFE/glass,  $\epsilon_r=2.5$

All microstrip lines  $W=2.2\text{mm}$

T1 3mm

T2 28mm

T3 12mm

T4 9mm

T5 5mm

T6 23 mm

T7 17mm

L1 7.5 turns 24swg enamelled copper wire, 3mm i.d.

L2 1.5 turns 24swg enamelled copper wire on ferrite core

## D2201UK 1000MHz Test Fixture

# Mouser Electronics

Authorized Distributor

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- Подбор аналогов;
- Консультации по применению компонента;
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- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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